

AllnGaP LED DICE

Part NO.: AOC-S10RxM-Au Series

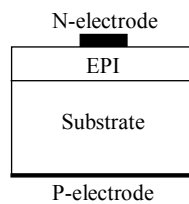
Features

- Red color emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-S10RxM Series is a red color emitting AllnGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for ultra-high brightness (UHB) automobile, display, and consumer electronic applications.

Chip Dimensions



Chip Size : 210 μ m \times 210 μ m \pm 25 μ m
 Bonding Pad : ϕ 105 μ m \pm 10 μ m
 Chip Thickness : 165 μ m \pm 25 μ m

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Typ.	Max	Unit
Forward Voltage	V _F	I _F =20mA	1.75	-	2.40	V
Reverse Current	I _R	V _R =5V	-	-	1.0	μ A
Dominant Wavelength	λ_d	I _F =20mA	616	-	630	nm
Max. Junction Temperature	T _{max}	-	\leq 120			$^{\circ}$ C
Max. DC forward current	I _f	T _a = 25 $^{\circ}$ C	\leq 30			mA
Max. pulse forward current (Pulse width 0.1 msec, frequency=1 kHz.)	I _{fm}	T _a = 25 $^{\circ}$ C	\leq 60			mA
Storage temperature	T _{stg}	Chip on tape	0 ~ 40			$^{\circ}$ C
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	\geq 280 mcd	\geq 320 mcd	\geq 360 mcd	\geq 400 mcd
S10 RSM	616 ~ 625 nm	-	Y32	Y36	Y40
S10 RMM	620 ~ 630 nm	-	Y32	Y36	Y40

Note:

All measurements are done with AOC's standard testing equipment.
 Luminance intensity is measured on bare chip.
 Above contents are subject to change without notice.
 Special requests are also welcome, please contact AOC's sale representative for any request..
 Characteristics curves are measured within TO-46 package

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